

ABSTRACT OF THE DISCLOSURE

Disclosed herein is a film bulk acoustic resonator (FBAR), an FBAR based duplexer device, and a manufacturing method thereof, which a plurality of sacrificial layer units are formed on a substrate wafer so as to be spaced apart from one another at regular distances, and device functional portions are formed on the sacrificial layer units, respectively. The device functional portions have a piezoelectric layer unit and a plurality of electrodes. Then, side wall and roof of protective formed by the use of dry film. After hardening the dry film, the wafer is cut into a plurality of the wafer sections so as to contain the device functional portions, respectively.